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November 2009

ISL9V5036S3S / ISL9V5036P3 / ISL9V5036S3

EcoSPARK® 500mJ, 360V, N-Channel Ignition IGBT

General Description

The ISL9V5036S3S, ISL9V5036P3, and ISL9V5036S3 are the next generation IGBTs that offer outstanding SCIS capability in the D²-Pak (TO-263) and TO-220 plastic package. These devices are intended for use in automotive ignition circuits, specifically as coil drivers. Internal diodes provide voltage clamping without the need for external components.

EcoSPARK® devices can be custom made to specific clamp voltages. Contact your nearest Fairchild sales office for more information.

Formerly Developmental Type 49443

Applications

- Automotive Ignition Coil Driver Circuits
- · Coil-On Plug Applications

Features

- Industry Standard D²-Pak package
- SCIS Energy = 500mJ at T_J = 25°C
- · Logic Level Gate Drive
- Qualified to AEC Q101
- RoHS Compliant



Package Symbol JEDEC TO-263AB JEDEC TO-220AB JEDEC TO-262AA D²-Pak ECG GATE COLLECTOR (FLANGE) COLLECTOR (FLANGE)

Device Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
BV _{CER}	Collector to Emitter Breakdown Voltage (I _C = 1 mA)	390	V	
BV _{ECS}	Emitter to Collector Voltage - Reverse Battery Condition (I _C = 10 mA)	24	V	
E _{SCIS25}	At Starting $T_J = 25^{\circ}C$, $I_{SCIS} = 38.5A$, $L = 670 \mu Hy$	500	mJ	
E _{SCIS150}	At Starting $T_J = 150$ °C, $I_{SCIS} = 30$ A, $L = 670 \mu$ Hy	300	mJ	
I _{C25}	Collector Current Continuous, At T _C = 25°C, See Fig 9	46	Α	
I _{C110}	Collector Current Continuous, At T _C = 110°C, See Fig 9	31	Α	
V_{GEM}	Gate to Emitter Voltage Continuous	±10	V	
P _D	Power Dissipation Total T _C = 25°C	250	W	
	Power Dissipation Derating T _C > 25°C	1.67	W/°C	
TJ	Operating Junction Temperature Range	-40 to 175	°C	
T _{STG}	Storage Junction Temperature Range	-40 to 175	°C	
T _L	Max Lead Temp for Soldering (Leads at 1.6mm from Case for 10s)	300	°C	
T _{pkg}	Max Lead Temp for Soldering (Package Body for 10s)	260	°C	
ESD	Electrostatic Discharge Voltage at 100pF, 1500Ω	4	kV	

Device Marking		Device	Package	Reel Size	е	Tape Width		Quantity
V5036S		ISL9V5036S3ST	TO-263AB	330mm		24mm		800
V5036P		ISL9V5036P3	TO-220AA	Tube	N/A			50
V5036S		ISL9V5036S3	TO-262AA	TO-262AA Tube		N/A		50
V5036S		ISL9V5036S3S	TO-263AB	TO-263AB Tube		N/A		50
Symbol		Parameter	unless otherwise n Test Con		Min	Тур	Max	Unit
	Characte		1		330	1		1
BV _{CER}	Collector to Emitter Breakdown Voltage		$R_G = 1K\Omega$, See	I_C = 2mA, V_{GE} = 0, R_G = 1K Ω , See Fig. 15 T_J = -40 to 150°C		360	390	V
BV _{CES}	Collector to Emitter Breakdown Voltage		$R_G = 0$, See F	$I_C = 10$ mA, $V_{GE} = 0$, $R_G = 0$, See Fig. 15 $T_J = -40$ to 150°C		390	420	V
BV _{ECS}	Emitter to Collector Breakdown Voltage		$\begin{array}{c} \text{le} \text{l}_{\text{C}} = \text{-75mA, V}_{\text{G}} \\ \text{T}_{\text{C}} = 25^{\circ}\text{C} \end{array}$	$I_C = -75 \text{mA}, V_{GE} = 0 \text{V},$ $T_C = 25 ^{\circ}\text{C}$		-	ı	V
BV_{GES}	Gate to Emitter Breakdown Voltage		$I_{GES} = \pm 2mA$	I _{GES} = ± 2mA		±14	-	V
I_{CER}	Collector to	o Emitter Leakage Current	$V_{CER} = 250V$,	$T_C = 25^{\circ}C$	-	-	25	μΑ
			$R_G = 1KΩ$, See Fig. 11	T _C = 150°C	-	-	1	mA
I _{ECS}	Emitter to	Collector Leakage Current	$V_{EC} = 24V$, See		-	-	1	mA
			Fig. 11	$T_C = 150$ °C	-	-	40	mA
R ₁	Series Gate Resistance					75	-	Ω
R ₂	1	nitter Resistance			10K	-	30K	Ω
	Characte		1, 404	- 0500 l		1 4 47	4.00	1 ,,
V _{CE(SAT)}	Collector to Emitter Saturation Voltage		$V_{GE} = 4.0V$	T _C = 25°C, See Fig. 4	-	1.17	1.60	V
V _{CE(SAT)}	Collector to Emitter Saturation Voltage		$I_C = 15A,$ $V_{GE} = 4.5V$	T _C = 150°C	-	1.50	1.80	V
ynamic	Characte	ristics						
Q _{G(ON)}	Gate Charge		1.7	I _C = 10A, V _{CE} = 12V, V _{GE} = 5V, See Fig. 14		32	-	nC
V _{GE(TH)}	Gate to Er	nitter Threshold Voltage	$I_C = 1.0 \text{mA},$	T _C = 25°C	1.3	-	2.2	V
			V _{CE} = V _{GE} , See Fig. 10	T _C = 150°C	0.75	-	1.8	V
V_{GEP}	Gate to Er	mitter Plateau Voltage	$I_C = 10A$,	V _{CE} = 12V	-	3.0	-	V
witching	Charact	eristics						
t _{d(ON)R}	Current Tu	rn-On Delay Time-Resistive	$V_{CF} = 14V, R_1 = 1\Omega,$		-	0.7	4	μs
t _{rR}		se Time-Resistive	$V_{GE} = 5V, R_G =$	$V_{GE} = 5V, R_G = 1K\Omega$ $T_J = 25^{\circ}C, See Fig. 12$		2.1	7	μs
t _{d(OFF)L}	Current Tu	rn-Off Delay Time-Inductive		V _{CE} = 300V, L = 2mH,		10.8	15	μs
t _{fL}	Current Fall Time-Inductive $V_{GE} = 5V, R_G = 1K\Omega$ $T_J = 25^{\circ}C, See Fig. 12$				-	2.8	15	μs

 $T_J = 25^{\circ}\text{C}$, L = 670 μH , R_G = 1K Ω , V_{GE} = 5V, See Fig. 1 & 2

TO-263, TO-220, TO-262

Thermal Characteristics

SCIS

 $R_{\theta JC}$

Self Clamped Inductive Switching

Thermal Resistance Junction-Case

500

0.6

mJ

°C/W

Typical Characteristics

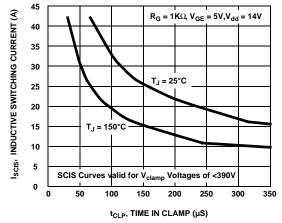


Figure 1. Self Clamped Inductive Switching Current vs Time in Clamp

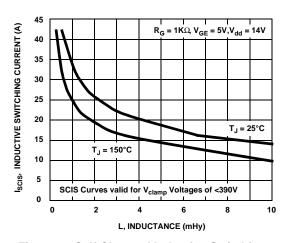


Figure 2. Self Clamped Inductive Switching Current vs Inductance

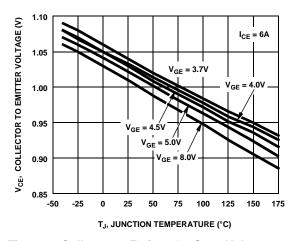


Figure 3. Collector to Emitter On-State Voltage vs Junction Temperature

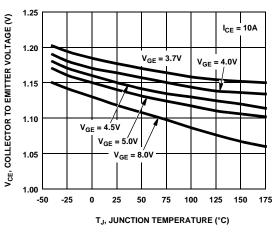


Figure 4.Collector to Emitter On-State Voltage vs Junction Temperature

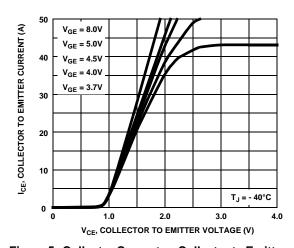


Figure 5. Collector Current vs Collector to Emitter On-State Voltage

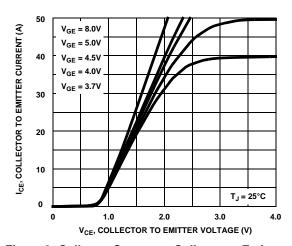


Figure 6. Collector Current vs Collector to Emitter On-State Voltage

T_J = 175°C V_{GE} = 8.0V V_{GE} = 5.0V V_{GE} = 4.5V V_{GE} = 3.7V T_J = 175°C V_{CE}, COLLECTOR TO EMITTER VOLTAGE (V)

Typical Characteristics (Continued)

Figure 7. Collector to Emitter On-State Voltage vs Collector Current

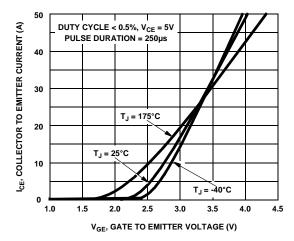


Figure 8. Transfer Characteristics

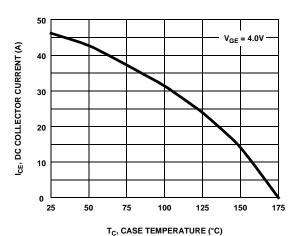


Figure 9. DC Collector Current vs Case Temperature

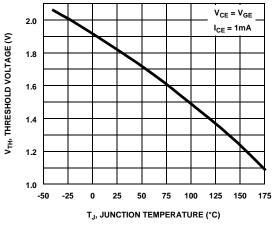


Figure 10. Threshold Voltage vs Junction Temperature

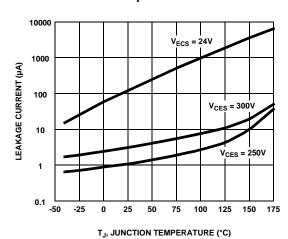


Figure 11. Leakage Current vs Junction Temperature

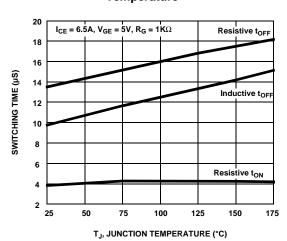
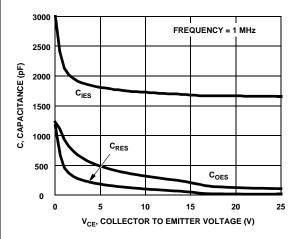


Figure 12. Switching Time vs Junction Temperature

Typical Characteristics (Continued)



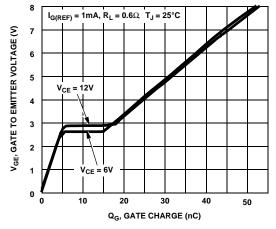


Figure 13. Capacitance vs Collector to Emitter Voltage

Figure 14. Gate Charge

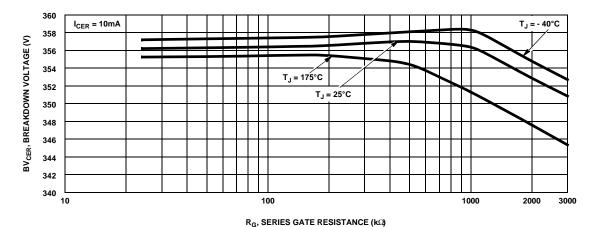


Figure 15. Breakdown Voltage vs Series Gate Resistance

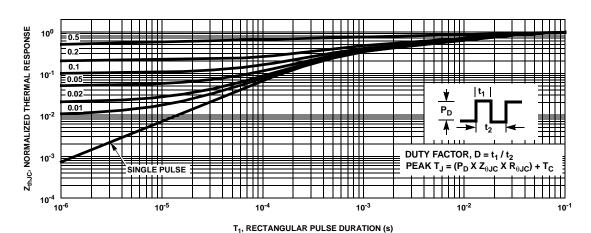
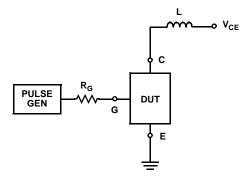


Figure 16. IGBT Normalized Transient Thermal Impedance, Junction to Case

Test Circuits and Waveforms



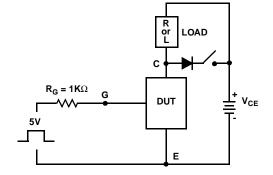
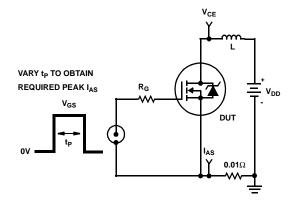


Figure 17. Inductive Switching Test Circuit

Figure 18. t_{ON} and t_{OFF} Switching Test Circuit





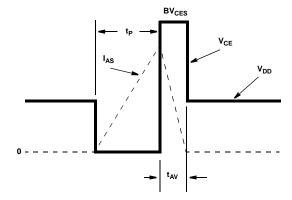


Figure 20. Energy Waveforms

SPICE Thermal Model JUNCTION REV 1 May 2002 ISL9V5036S3S / ISL9V3536P3 / ISL9V5036S3 CTHERM1 th 6 4.0e2 CTHERM2 6 5 3.6e-3 CTHERM3 5 4 4.9e-2 RTHERM1 CTHERM1 CTHERM4 4 3 3.2e-1 CTHERM5 3 2 3.0e-1 CTHERM6 2 tl 1.6e-2 6 RTHERM1 th 6 1.0e-2 RTHERM2 6 5 1.4e-1 RTHERM3 5 4 1.0e-1 RTHERM2 CTHERM2 RTHERM4 4 3 9.0e-2 RTHERM5 3 2 9.4e-2 RTHERM6 2 tl 1.9e-2 5 SABER Thermal Model SABER thermal model ISL9V5036S3S / ISL9V5036P3 / ISL9V5036S3 RTHERM3 CTHERM3 template thermal_model th tl thermal_c th, tl ctherm.ctherm1 th 6 = 4.0e2ctherm.ctherm2 65 = 3.6e-3ctherm.ctherm3 5 4 = 4.9e-2ctherm.ctherm4 43 = 3.2e-1RTHERM4 CTHERM4 ctherm.ctherm5 3 2 = 3.0e-1 ctherm.ctherm6 2 tl = 1.6e-2 rtherm.rtherm1 th 6 = 1.0e-2 3 rtherm.rtherm2 6 5 = 1.4e-1 rtherm.rtherm3 5 4 = 1.0e-1 rtherm.rtherm4 4 3 = 9.0e-2RTHERM5 CTHERM5 rtherm.rtherm5 3 2 = 9.4e-2rtherm.rtherm6 2 tl = 1.9e-2 2 RTHERM6 CTHERM6 CASE





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